

Alessandro Caratelli

on behalf of the CMS Tracker ASICs designers team

Requirements for the high luminosity tracker upgrade [1]

SYESTEM STUDIES

Phase-2 upgrade tracker requirements:

- Higher luminosity
- From 20 to 200 pileup events per BX
- Increase radiation tolerance
- Reduced material budget
- Participate in the L1 trigger
- Improve trigger performance



- Increase granularity
- Introduction of a pixelated sensor in OT
- Radiation tolerance up to 100 Mrad
- Quick and on-chip particle discrimination
- Higher trigger rate (1MHz) and longer latency (12.5 μ s)
- Power density < 100 mW/cm²
- Add tracking information to the Level-1 trigger decision



A novel particle detector electronic system

SYESTEM STUDIES

The outer tracker detector can provide for every event additional information for the trigger decision leading to a significant improvement of the particle recognition efficiency



The complete real time tracker readout is not feasible



HOW? The readout electronics in the detector can send pre-selected information for the Level-1 event reconstruction





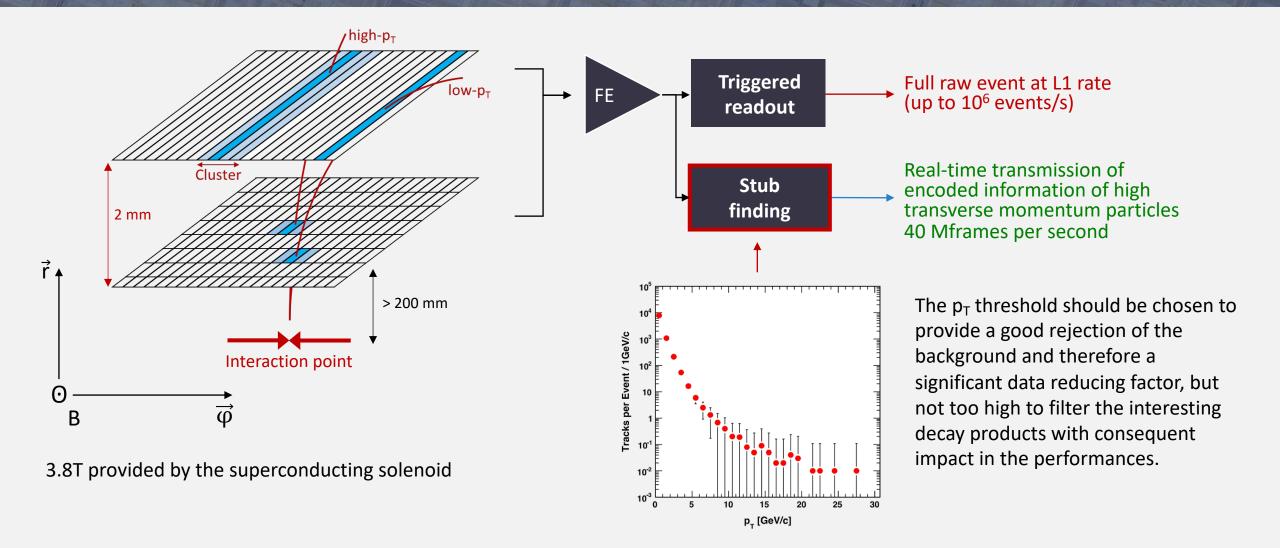
Intelligent pixel particle detector capable to locally self-select interesting signatures of particles interesting for the physics, without relying on an external trigger system



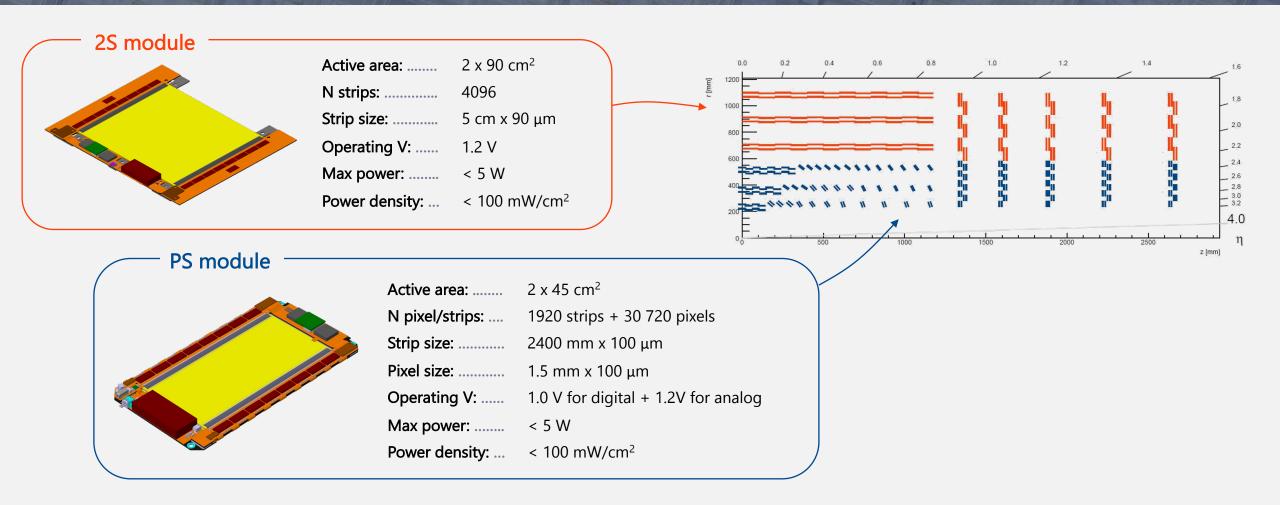
This approach allows for a significant data reduction efficiency improvement

Detector capable of providing particle transverse momentum information in addition to simple geometrical positioning and energy measurements

An intelligent particle tracking system based on p_T discrimination



The CMS Outer Tracker [1, 2]



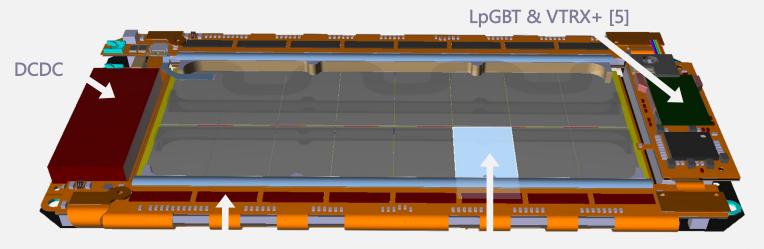
[1] CMS collaboration. "The phase-2 upgrade of the CMS tracker." CMS-TDR-014 (2017).

[2] Abbaneo, Duccio. "Upgrade of the CMS Tracker with tracking trigger." Journal of Instrumentation 6.12 (2011): C12065.

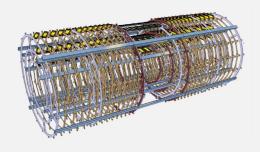
CONCLUSIONS

TEST RESULTS

The Pixel-Strip module

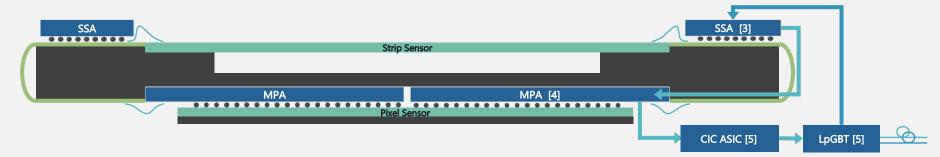


13296 Modules
44 Mstrips + 174 Mpixels
200m² of silicon area



16 x SSA ASICs (Strip ROC) [3]

16xMPA (Pixel ROC + stub finding) [4]



[3] Caratelli, Alessandro, et al. Characterization of the first prototype of the Silicon-Strip readout ASIC (SSA). No. CMS-CR-2018-286. 2018.

[4] Ceresa, Davide, et al. Characterization of the MPA prototype, a 65 nm pixel readout ASIC with on-chip quick transverse momentum discrimination capabilities. No. CMS-CR-2018-279. 2018.

[5] Moreira, Paulo. "The LpGBT project status and overview." ACES. 2016.

[6] Nodari, Benedetta, et al. A 65 nm data concentration ASIC for the CMS outer tracker detector upgrade at HL-LHC. No. CMS-CR-2018-278. 2018.

MPA and SSA ASICs: system level architecture choices

SYSTEM STUDIES

Initial open design choices:

- Define which functionality are implemented in the SSA and which in the MPA
- Minimise system power requirements
- Minimize bandwidth requirements
- Maximize the particle recognition efficiency
- Bandwidth among ASICs
- Data encoding
- Transmission FIFOs depth
- Data compression
- Particle hit clustering at SSA level
- Several others

Functionality and the efficiency depends on physics statistics, particle rates and hit occupancy (no simple test vectors)

Becomes necessary a Simulation framework capable of providing:

System Studies and performances evaluation

Design Verification

- **Study and compare** different system implementation
- Evaluate tradeoff between performances and power optimization
- Report efficiency parameters by comparison with a system reference model
- Evaluate the efficiency of the particle recognition and of the data readout
- Realistic stimuli generation from Monte-Carlo simulations of complex interactions in high-energy particle collisions

MPA and SSA ASICs: system level architecture choices

SYSTEM STUDIES

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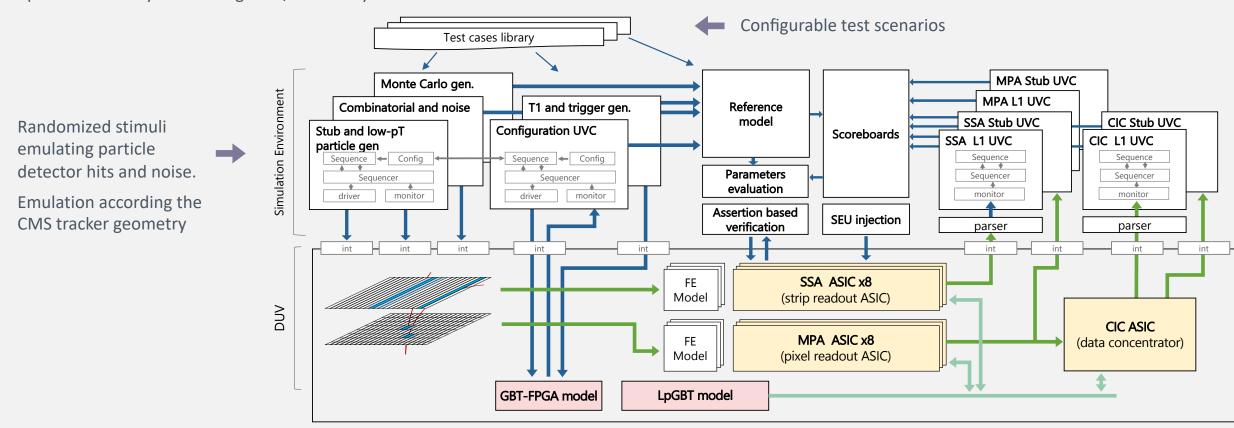
System Studies and performances evaluation

Design Verification

- Verify the RTL implementation and the chip-set functionalities
- Generation of realistic activity information for precise power analysis
- Verify post-layout netlist
- Verify at clock-cycle level precision the subsystems integration and the communication among modules the ASICs

System level simulation framework [7]

Implemented in: SystemVerilog HDL / UVM + Python

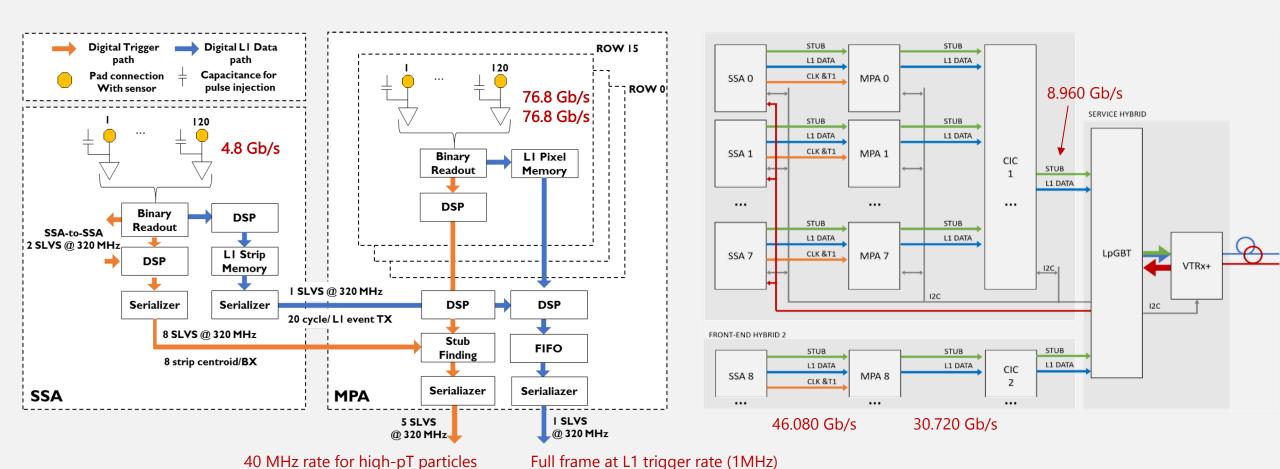


[7] Caratelli, Alessandro, et al. "System Level simulation framework for the ASICs development of a novel particle physics detector." 2018 14th Conference on Ph. D. Research in Microelectronics and Electronics (PRIME). IEEE, 2018.

1.6 Gb/s - latency: < 500 ns

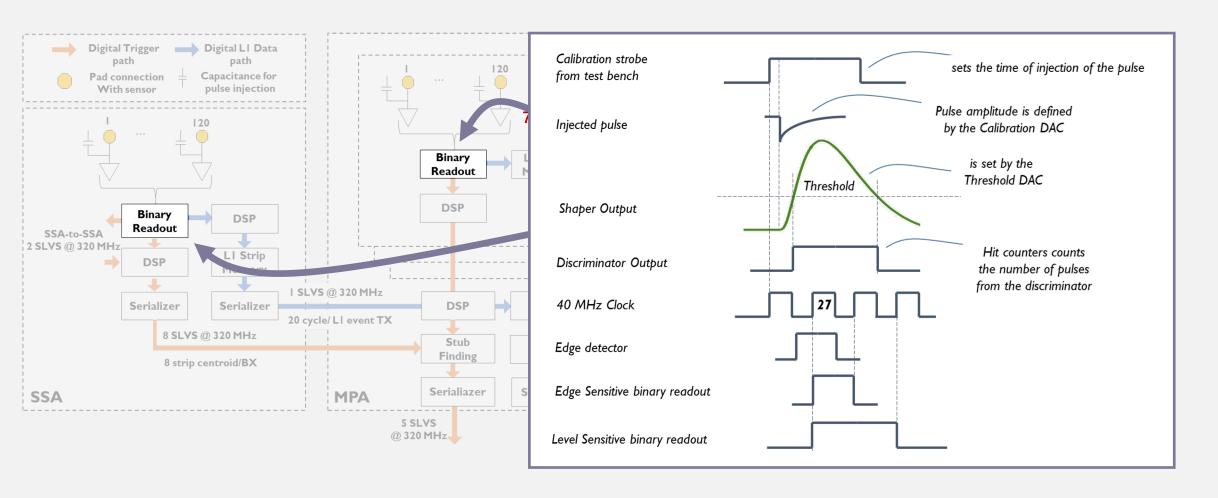
System architecture definition [8]

SYSTEM STUDIES



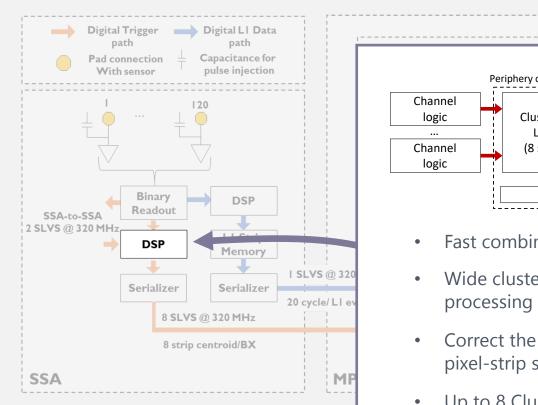
[8] A. Caratelli, D. Ceresa, S. Kloukinas, S. Scarfi et al. Readout architecture for the Pixel-Strip module of the CMS Outer Tracker Phase-2 upgrade. No. CMS-CR-2016-405.

320 Mb/s



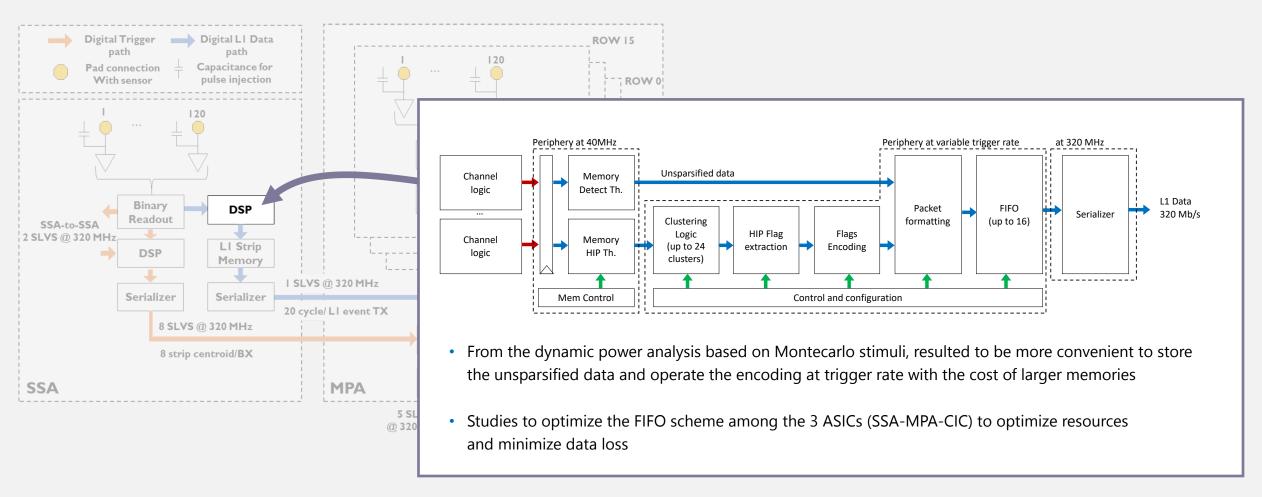
[9] D. Ceresa, A. Caratelli, G. Bergamin, J. Kaplon, K. Kloukinas, S. Scarfì "MPA-SSA, design and test of a 65nm ASIC-based system for particle tracking at HL-LHC featuring on-chip particle discrimination." 2019 IEEE Nuclear Science Symposium and Medical Imaging Conference (NSS/MIC). IEEE, 2019.

SYSTEM STUDIES

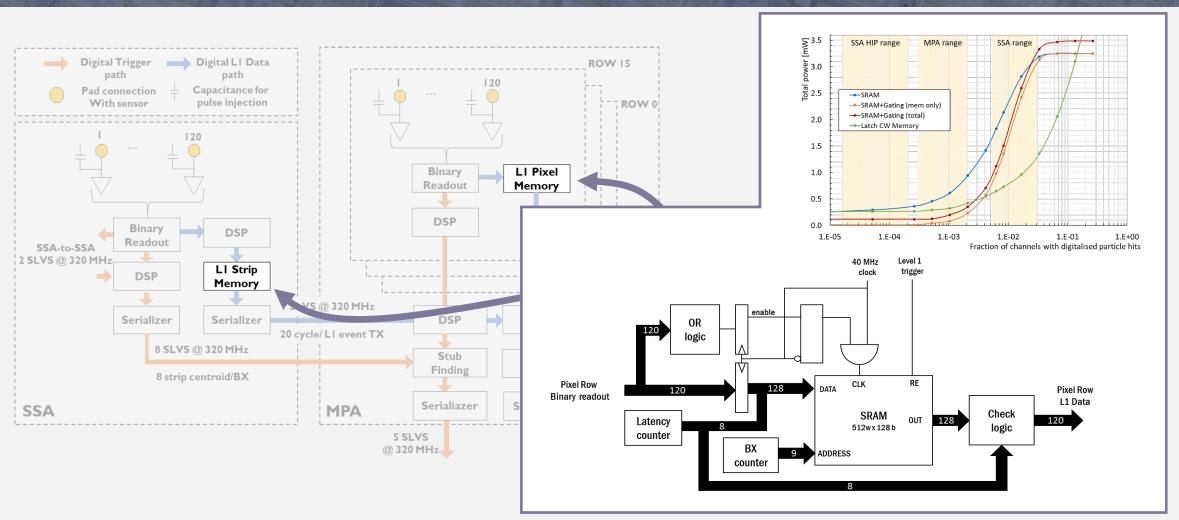


- Periphery operating at bunch crossing event rate Periphery at 320MHz Clustering Coordinate Centroids Parallax Data Stub Data encoding and Serialiser Logic extraction formatting correction 2.56 Gb/s (8 stubs) ordering Control and configuration
 - Fast combinatorial **clustering** at event rate to limit cross-talk effect
 - Wide clusters represents not interesting events: are filtered to optimize bandwidth and processing power.
 - Correct the parallax error of approximating the cylindrical geometry with planar pixel-strip sensors.
 - Up to 8 Cluster Centroids coordinates are transmitted per every event to the MPA coincidence logic for the Stub generation and the transverse momentum discrimination

[9] D. Ceresa, A. Caratelli, G. Bergamin, J. Kaplon, K. Kloukinas, S. Scarfì "MPA-SSA, design and test of a 65nm ASIC-based system for particle tracking at HL-LHC featuring on-chip particle discrimination." 2019 IEEE Nuclear Science Symposium and Medical Imaging Conference (NSS/MIC). IEEE, 2019.

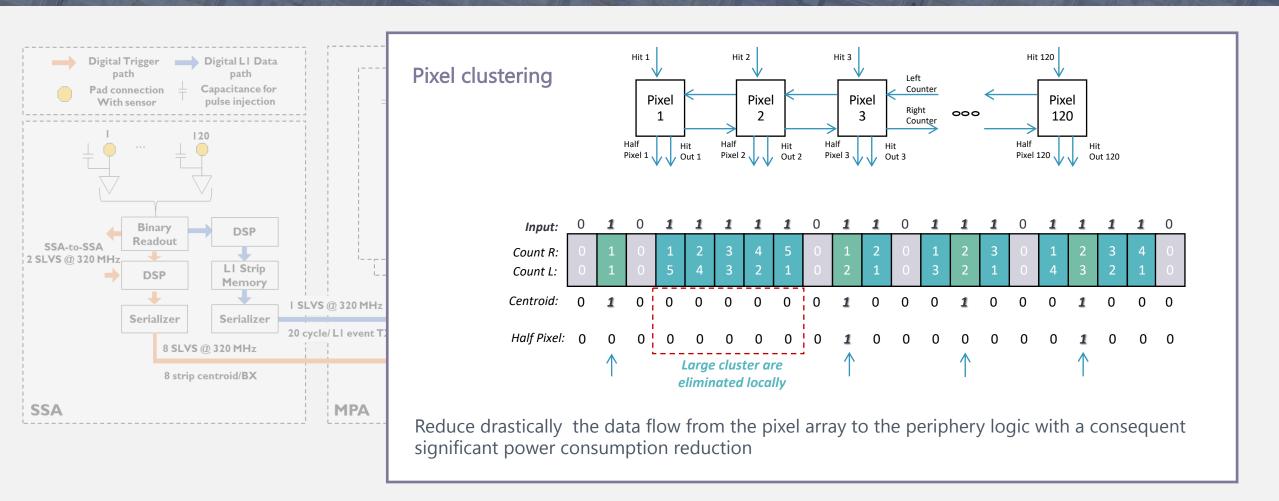


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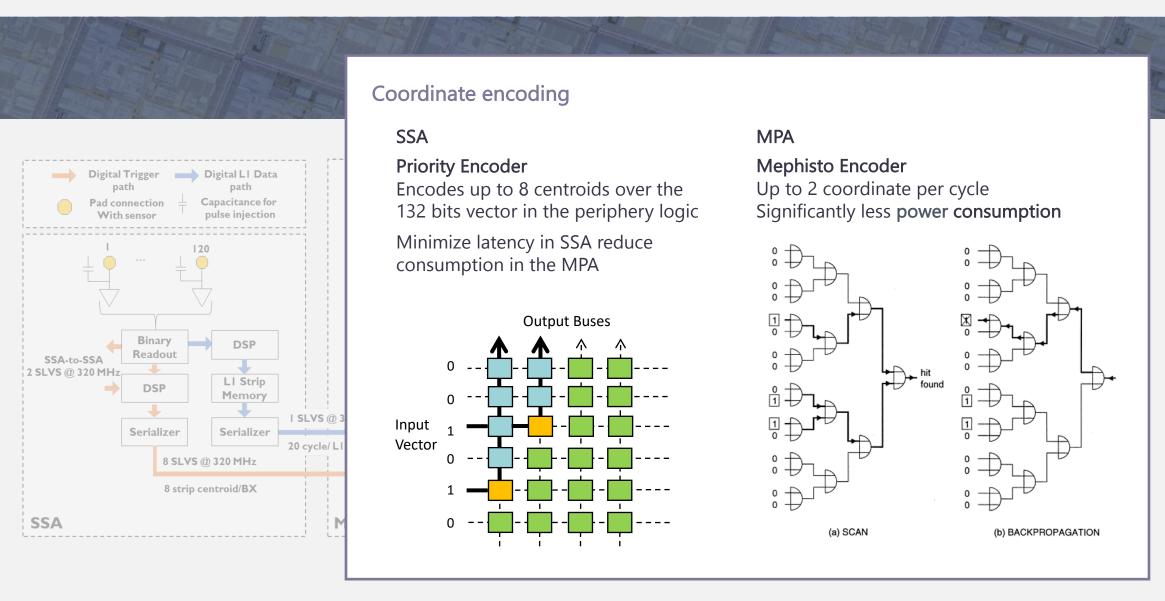


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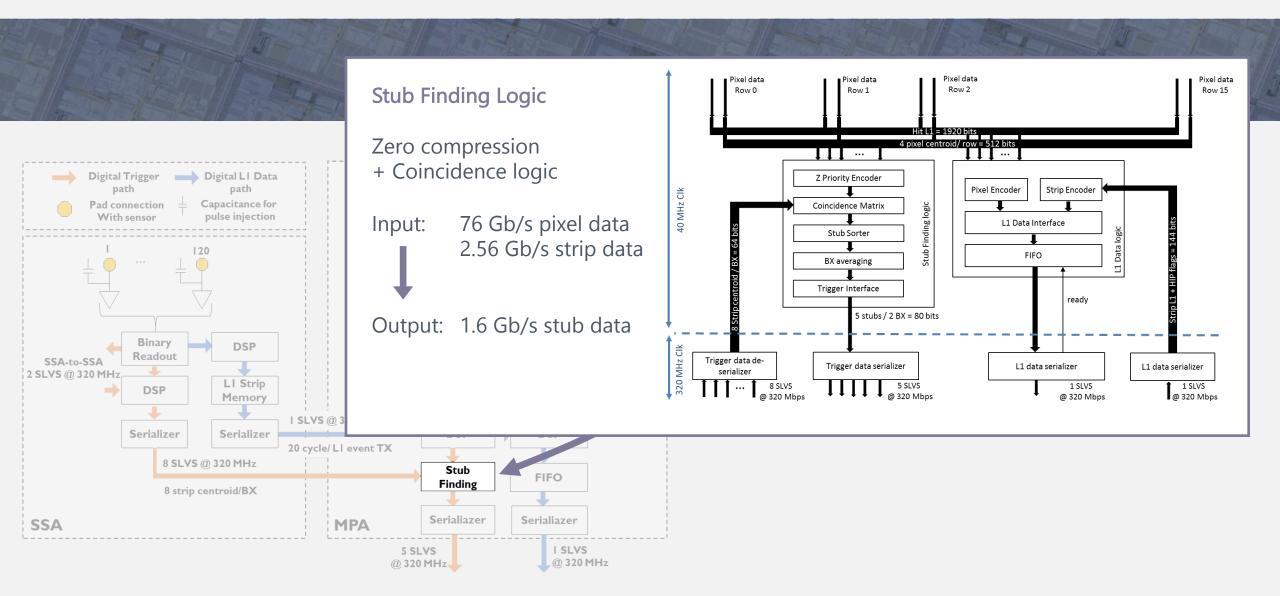
System architecture definition



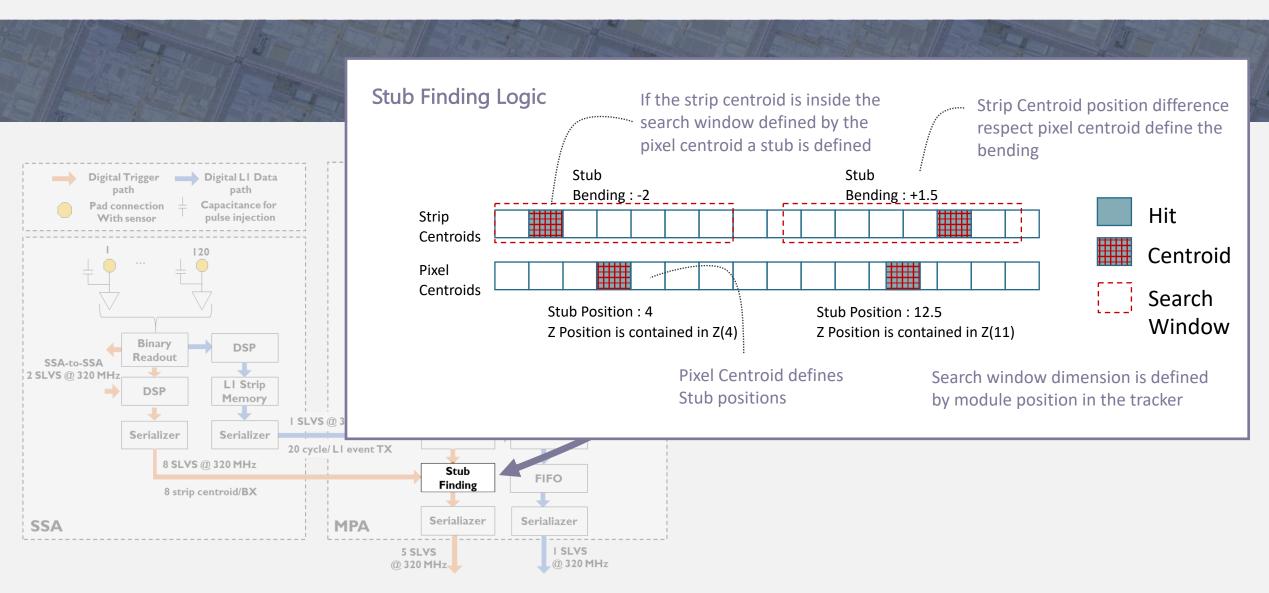
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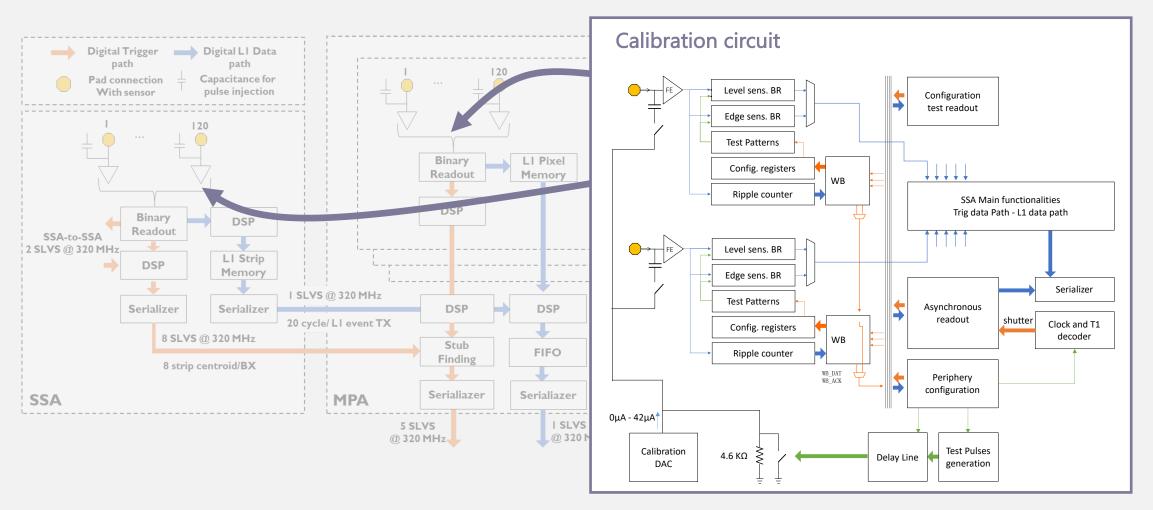
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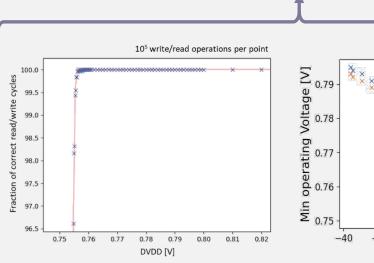
Design for Testability

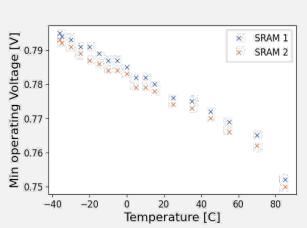
Memory Built-In-Self-Test

- Test full memory functionality in <10 ms
- Results saved in internal registers accessible via slow-control
- Few additional hardware self contained hierarchical block
- Clock gating during normal operation (only leakage power)

Periphery Scan Chain

- FSM Easy to access standardized approach with TRL
- 92% of fault coverage in SSA (300ms)
- ~95% of fault coverage and 25k ff in MPA (750ms)





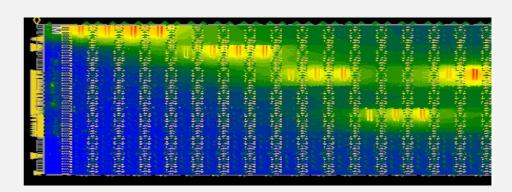
Logic Built-In-Self-Test for pixel array

- FSM embedded in Pixel Array logic and vectors from configuration
- Requires compression / decompression logic
- ~90% coverage

Power Reduction Methodology

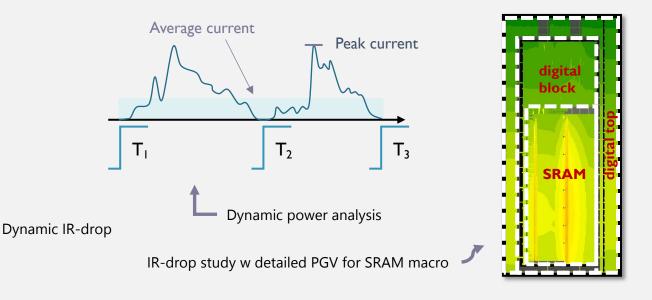
Power optimization

- Clock gating in all configuration registers and logic
- Architecture studies to minimize power consumption
- Use Multi-VT standard cells
- Use gated SRAM blocks
- Multi-supply voltage (1.0V 1.2V)
- Find power hungry and low activity blocks and optimize their implementation



Power study:

- Static and Dynamic power analysis
- Voltage drop analysis on different scenario
- Power-Grid-View (PGV) for Macro



Total Ionizing Dose effects hardening

Digital domain:

- 9-tracks library selected as compromise between power consumption and radiation tolerance considering the operating range -40°C / 0°C
- Characterization of the digital cells parameters (prop. delay, transition time, setup/hold, etc.) for radiation corner
- Increased margins for TID degradation (setup uncertainty jitter + additional 8% of clock period reduced max transition derate factors)
- Due to narrow channel effects → Removed minimum-width cells (D0, D1) and delay elements
- Only thin-oxide devices → 1.2V max (CMOS IO and SLVS)
- Custom ESD structures latch-up resistant

Memories:

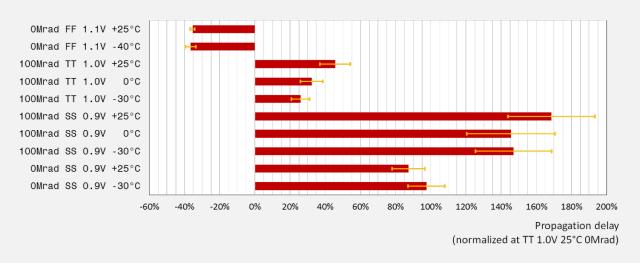
- A custom memory compiler allowed to generate a SRAM with cell transistor featuring nMOS W > 200 nm pMOS W > 500 nm
- Protection against latch-up is reached by placing p⁺ guard bands between n⁻ regions.

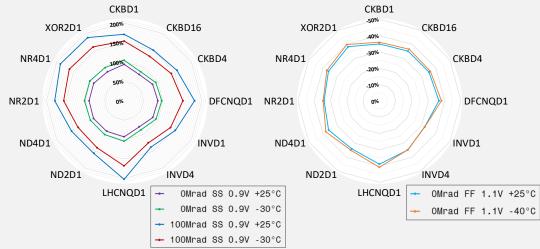
Usage of ELT devices in input stage:

- To prevent the radiation induced drain-to-source leakage current increase due to the charge trapped in the shallow trench isolations (STI).
- To mitigate the 1/f noise increase on irradiated devices due to side-effects of the STI region in nMOS operated at low drain current.

Digital library choice and delay corner comparison

- Supply voltage scaling
- 9 tracks library chosen as compromise between power consumption and radiation tolerance
- Temperature inversion effect prevent the SSA from using a high-Vt library cells at 0.9V.
- Mix of standard-Vt and low-Vt digital cells at 1.0V+10% as compromise of power consumption, memory operation and propagation delay at -40° C





Single Event Effects tolerance

State machines

- Triple module redundancy (FULL)
- Triplicated Clock-trees
- Triplicated Reset distribution
- FF minimum distance 15um

Latch FIFOs

- Control and header fields triplicated
- Data latches not protected

Data pipeline

 No SEU protection applied due to limited power budget

Clock tree

- Clock tree triplicated
- The non-triplicated logic uses the voted clock in critical areas
- The non-triplicated logic uses one of the branches in non-critical areas:
 - Simplify scan-chain insertion
 - Helps in reducing buffering for hold fix (power)
 - Allow for CPPR on the 3 branches

Triplicated pads for

- ClockControl
- ResetScan-Chain IOs

Configuration registers

- Triple module redundancy with error detection and self-correction
- Clock enabled only during
 - o asynchronous readout operation,
 - configuration operations
 - self-correction

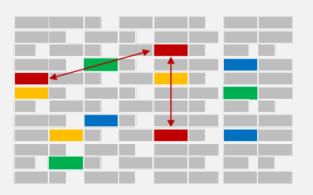
Glitch filters

- Reset inputs
- TEST-MODE signal
- Scan-chain TEST POINTS control (on the control of the system clock / test clock selection multiplexers)

Single Event Effects tolerance

Physical implementation

- Use of instance space groups among triplicated registers
- Avoid logic simplification by synthesis and P&R flow
- Spacing for clock and reset:
 - After CTS locate the critical cells and impose a minimum distance
 - procede in successive ECO placements and ECO routing steps



Functional simulation

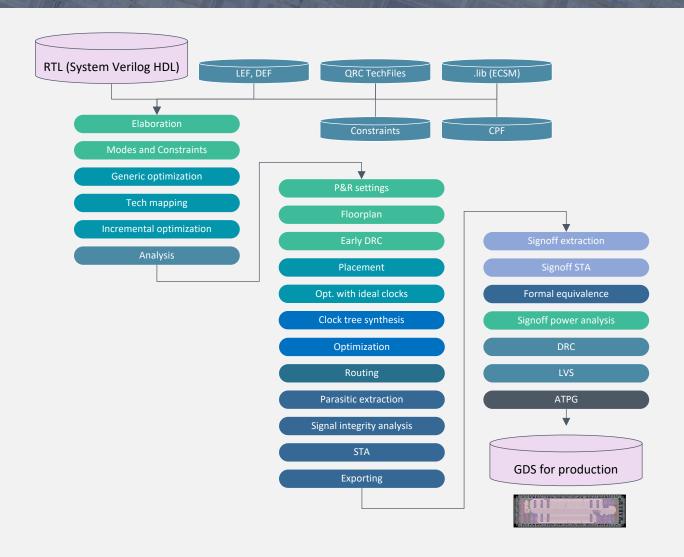
- System Verilog UVC for randomize the injection (constrained from the specific test case)
- The randomization is constrained accordingly: Error probability, average SEE rate, minimum time split, etc..
- Injection of single event effects in multiple ASICs at the same time to evaluate the consequences that SEE in an ASIC have on the other ASICs part of the chipset
- Possibility to focus the SEU injection on particular module or subsystem and evaluate the effect at system level
- Possibility to inject SEU in hundred of cells per clock cycle (register grouped in non-interacting categories)

Additional checks

- Script to verify that no triplicated instance is optimized out
- Script to verify placement constraints after chip assembly

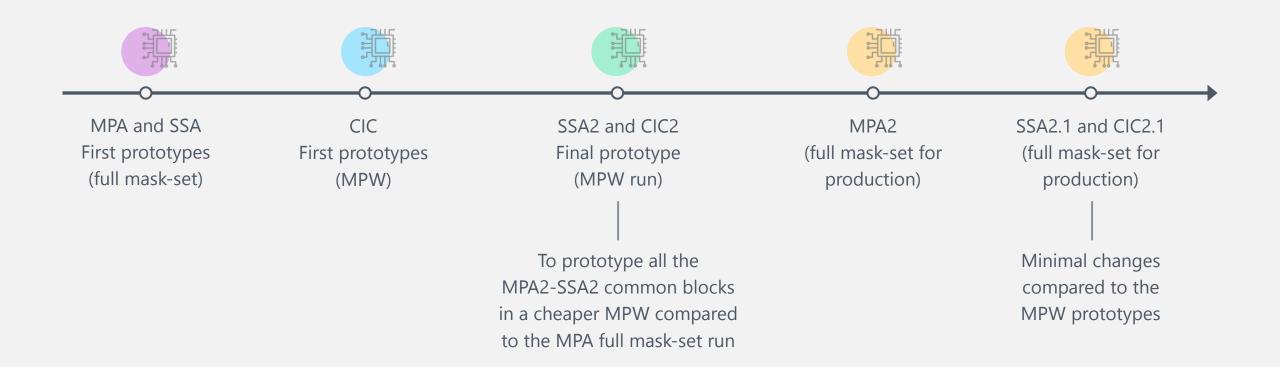
CONCLUSIONS

Physical Implementation flow

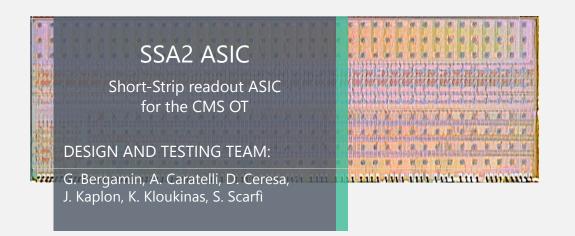


- Digital-on-top design flow
- Hierarchical implementation
- Multi supply voltage 1.0 V ± 10% 1.2 V ± 10%
- 3 independent power and ground domains to reduce noise coupling with guard-ring isolation
- Multi-Vt design (Low-Vt used only in critical timing arcs)
- C4 bump floorplan + wirebond for wafer probing
- Complex CTS and timing closure due to triple clock tree balancing and SEU hardening
- Constraints for TMR and digital cells placement
- Skew balancing among triplicated and voted clock trees
- Strip cell sampling clock guarantees <200ps skew in all corners
- Non-default CTS rules to mitigate cross-coupling
- QRC extracted information already at the optimization stage due to design size

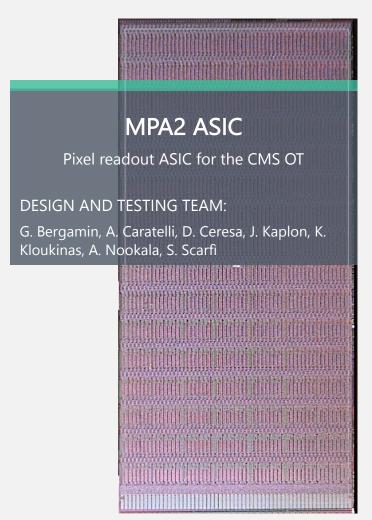
MPA-SSA-CIC Timeline



The ASICs





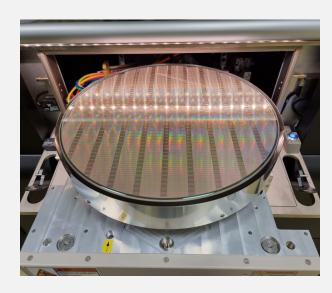


ASICs testing

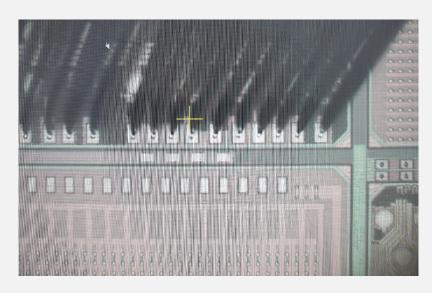
- The SSA, the MPA and the CIC were produced in a full mask-set engineering run
- The first 6 wafers have been tested at wafer level
- Test routine includes:
 - Scan-chain test for production defects
 - Functional test of digital circuits

- Analog bias parameter caracterization
- Front-end caracterization

- Noise analysis
- Serial ID and trimming in e-fuses
- The wafer have been diced and the chip bonded on carrier boards for radiation tests and detailed cractarization







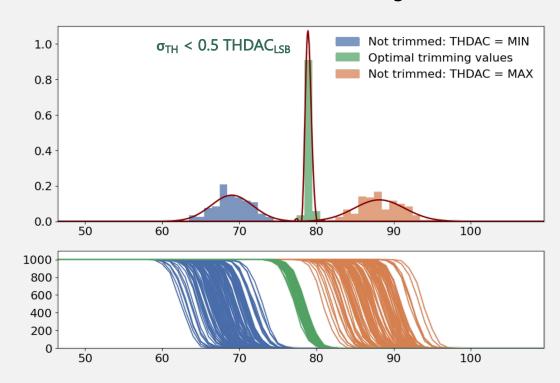
TEST RESULTS CONCLUSIONS INTRODUCTION SYSTEM STUDIES ASICS ARCHITECTURE **DESIGN METHODOLOGY**

SSA test results

0.08 Shaper pulse reconstruction Wafer 1 9000 chips tested mean = 55.02 mV/fCWafer 2 Wafer 3 0.07 by injecting a known charge via the SSA calibration system and acting on mean = 55.23 mV/fCWafer 6 threshold, calibration pulse delay-line and clock deskewing DLL. 0.06 1.25 mV/fC Peaking Time = 19.3 ns distribution 0.05 mean = 54.36 mV/fCstd = 1.29 mV/fC0.04 -20Normalize 80.0 0.02 Peaking time < 25ns Threshold Voltage [mV] $\overline{OFS_{FE}} = 5.54mV$ with linear behavior and 0.01 up to 8fC 0.00 Normalised distribution Normal 50 FE Gain Mean [mV/fC] -80Gain and offset distributions ₹ 1.29 fC -100for a non-trimmed SSA ASIC 1.72 fC 2.15 fC 0.1 2.58 fC -1200.0 70 10 20 60 10 Front-End Offset [mv]

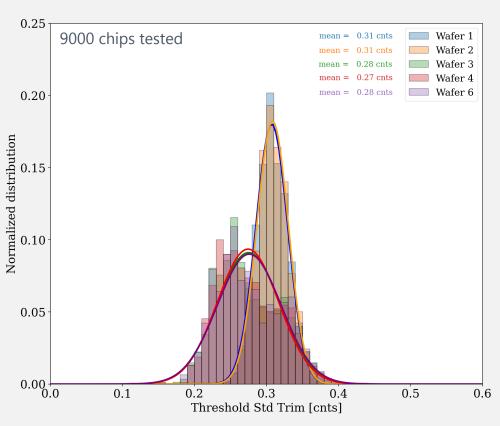
Time [ns]

SSA Threshold trimming

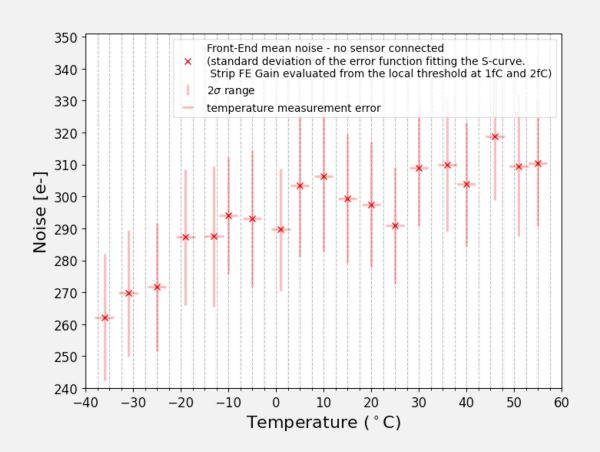


Trimming performed at 2.0 fC.
Threshold spread evaluate for 2.0 fC and 1.25fC

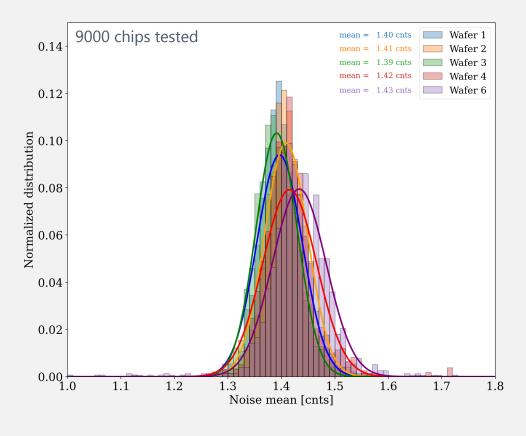
SSA Threshold distribution after trimming



SSA Analog Front-End Noise vs Temperature



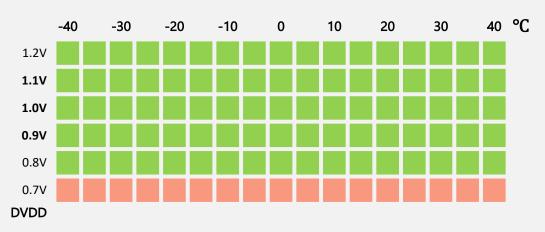
SSA Front-end noise measurements



Channel input noise evaluated as the standard deviation of the error function fitting the S-Curves (1.25 fC and 2.0 fC)

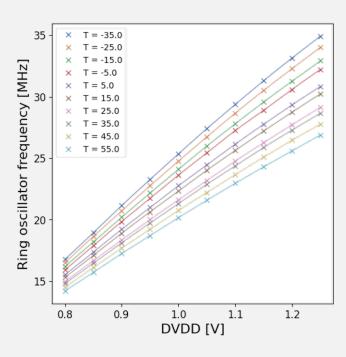
Temperature Characterization summary

No errors or timing issues observed on digital logic



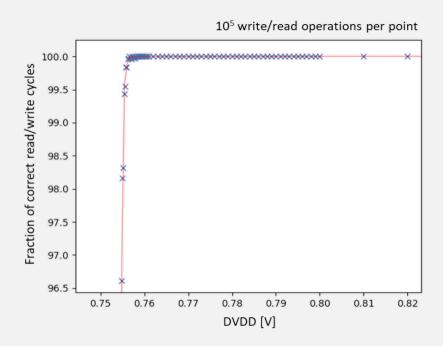
- No errors or issues observed in analog FE
- Bias structures variation within compensating range
- FE noise change within expectation

- Full set of digital functionalities tests
- Tests of memories (with BIST) and configuration
- Characterization of all bias parameters
- S-Curve for FE Gain, Noise and Trimming
- ADC, E-Fuses, Voltage swipes and several others



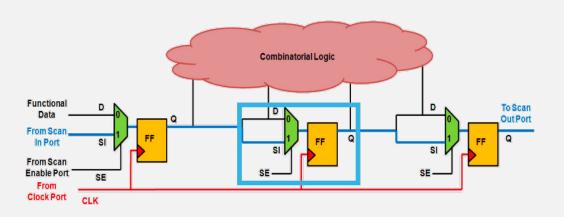
Memory Built-In-Self-Test

- Test full memory functionality in <1 ms
- Results saved in internal registers accessible via slow-control
- Clock gating during normal operation (only leakage power)



Scan Chain

- 92% of fault coverage in SSA ASIC
- Custom approach for triplicated design
- SHIFT, RESET and CAPTURE tests
- A total of ~950 test vectors required
- Full test duration < 300 ms
- Scan-chain in SSA operates correctly up to 20MHz

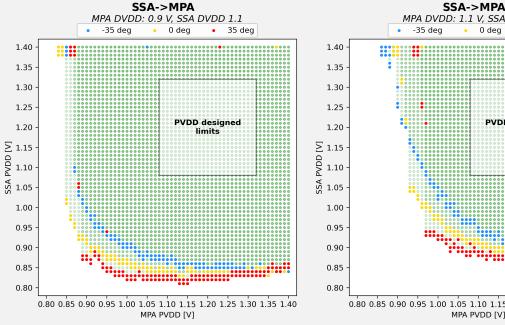


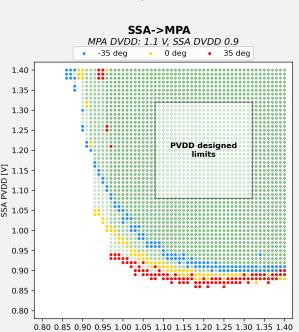
CONCLUSIONS INTRODUCTION ASICS ARCHITECTURE **DESIGN METHODOLOGY TEST RESULTS** SYSTEM STUDIES

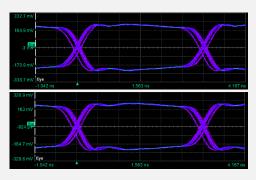
MPA-SSA test results

SSA → MPA Communication

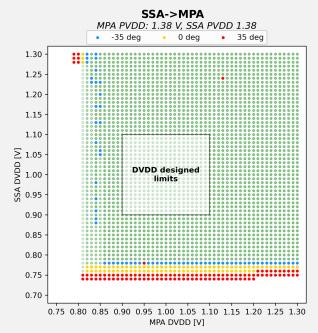
- No phase aligner at MPA input due to power restrictions
- The communication rely on precise design of the timing
- SSA-MPA communication timing was verified in static timing analysis and simulated post-layout in all cross-corner combinations (UVM verification environment)

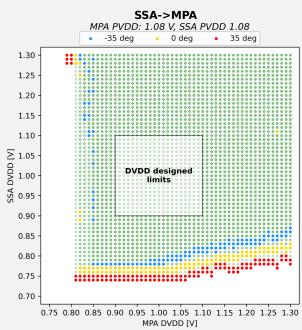












Total Ionizing Dose characterization

X-ray TID Characterization summary

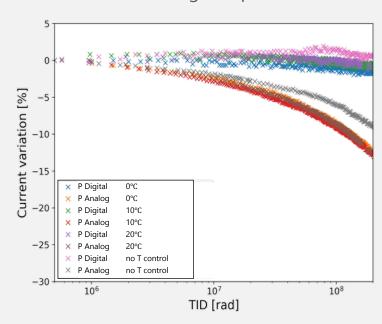
- 4 chips have been irradiated up to 200 Mrad and 1 chip up to 350 Mrad
- No errors or timing issues observed on digital logic



- Bias structures variation within compensating range
- FE noise change within expectation
- ADC reference voltage variation larger then expected:
 - Needed changing the target reference voltage to keep stable the DAC output up to 200Mrad.

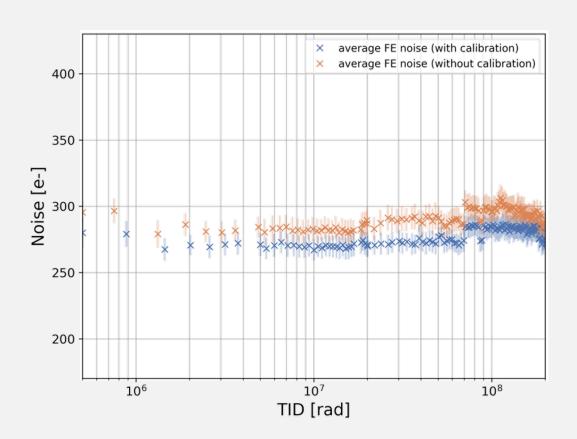
TID Test routine:

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- Tests of memories (with BIST) and configuration
- Characterization of all bias parameters
- S-Curve for FE Gain, Noise and Trimming
- ADC, E-Fuses, Voltage swipes and several others

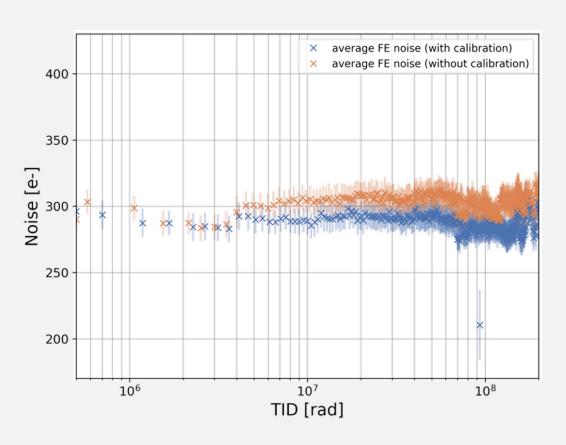


SSA Front-End equivalent noise evolution with TID and temperature

SSA 2.1 average FE noise* vs TID at -10°C



SSA 2.1 average FE noise* vs TID at +20°C



^{*} FE noise evaluated on the S-Curves – 2 fC internal charge injection – Sensor inputs floating

SSA Single-Event Effect tests with heavy ions

SYSTEM STUDIES

SEE testing carried out in UCL at Louvain-la-Neuve, Belgium

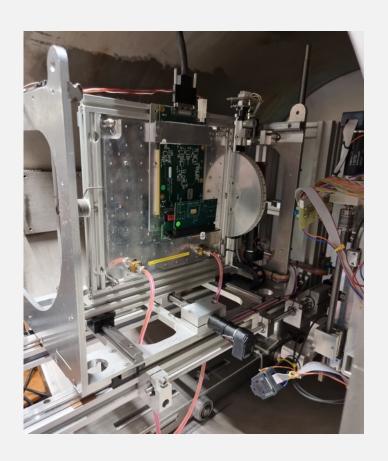
No hard errors observed

- No loss of control observed
- No loss of synchronisation observed
- No chip looks or control errors in general

Configuration system error-free

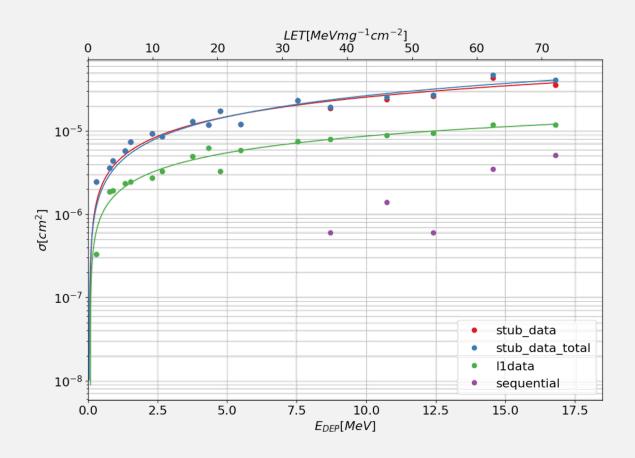
- Verified by readout and comparison of full chip configuration at each test iteration (30 seconds)
- SEU correction counter monitoring

Limit cross section for 10h test $\sim 5.10^{-9}$ cm²



SSA Single-Event Effect tests with heavy ions

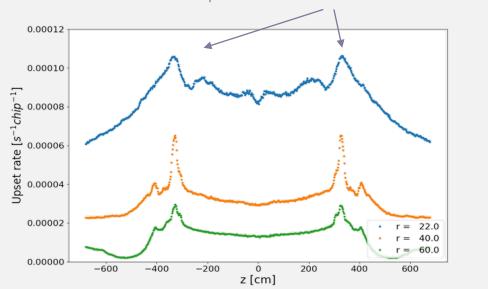
Stub and L1 data SEE cross-section:



Bit error rate estimation

(based on OT fluxes from FLUKA simulation)

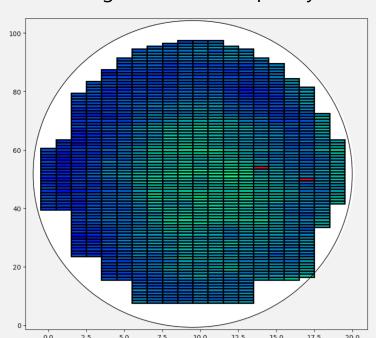
	Maximum SSA bit-error rate expected
Stub data	1.2·10 ⁻¹¹ BX ⁻¹
L1 data (12.6 us latency)	$1.0 \cdot 10^{-11} \text{ BX}^{-1}$
L1 data (2.5 us latency)	$9.7 \cdot 10^{-11} \text{ BX}^{-1}$



SSA Wafer Probing - process and analog performance

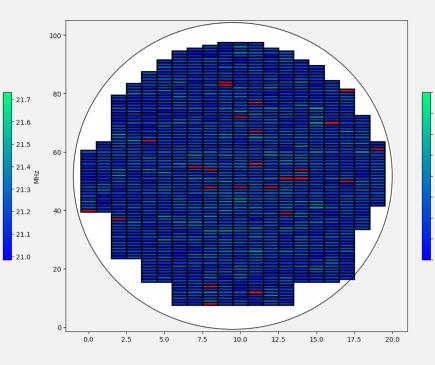
SYSTEM STUDIES

Ring oscillators Frequency



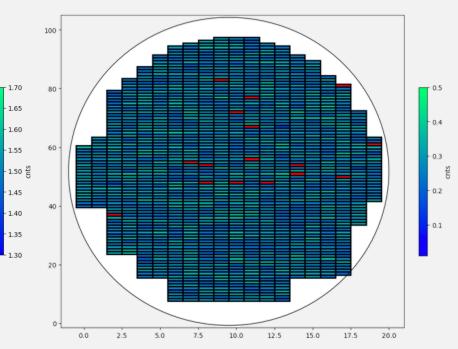
The SSA includes different types of ring oscillator to monitor variations in: Process – Temperature – Total Ionizing Dose

FE Noise Performance Tests



- Map of the average FE noise
- Cut criteria noise < 1.7 LSB

FE Threshold Trimming

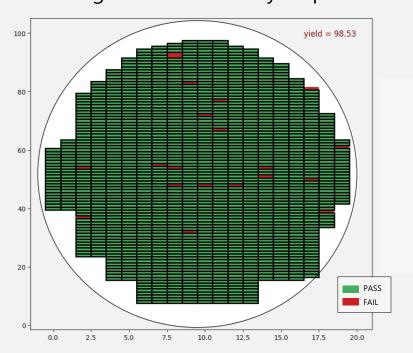


- Map of the threshold spread after the trimming procedure
- Cut criteria std(Th) < 0.5 LSB

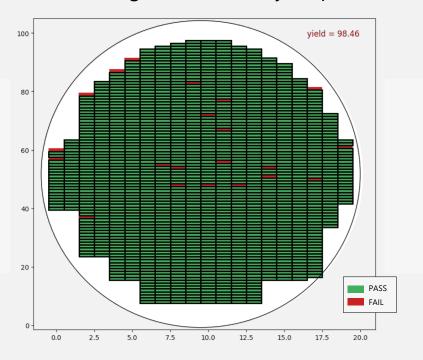
SSA Wafer Probing - yield

SYSTEM STUDIES

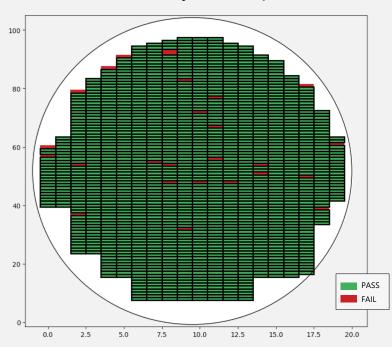
Digital Tests summary map



Analog Tests summary map



Total yield map



- Stub data [0.9V, 1.0V, 1.1 V]
- L1 data [0.9V, 1.0V, 1.1 V]
- Memory BIST [0.8V, 1.0V, 1.2 V]
- Configuration and all other digital functionalities

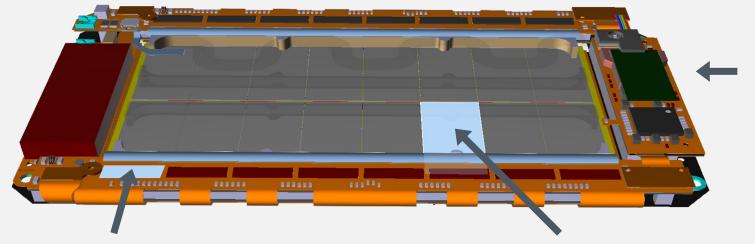
- Analog bias calibration
- FE functionality
- FE Threshold trimming
- Noise analysis

Overall yield (all tests) > 95%

Summary

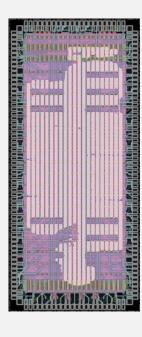
- System-level studies allowed to define the architecture of the PS-Module ASICs
- After testing the prototypes, the final version of the ASICs (MPA2, SSA2 and CIC2) have been submit to production in a full mask-set engineering run.
- The first wafers arrived at CERN, have been diced and tested
- The tests on the final version of the chips show results in agreement with the expectation
 - Front-end performances fulfil specifications
 - X-Ray TID test confirms radiation harness up to 200 Mrad
 - Heavy Ion test confirms the functionality of the chosen hardening strategy
 - o Climatic chamber tests shows a parameter variation within the calibration range
- Wafer-level testing show a high yield, which allow us to move to the next step of ordering the production wafer and define the automated production test procedure.

Summary



CIC2 ASIC

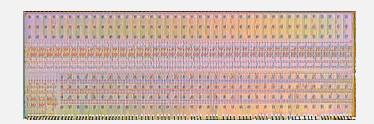
L. Caponetto, G. Galbit, S. Scarfì, B. Nodari, S. Viret, A. Caratelli, D. Ceresa (IP2I Lyon university)



SSA2 ASIC

DESIGNED AND TESTED BY:

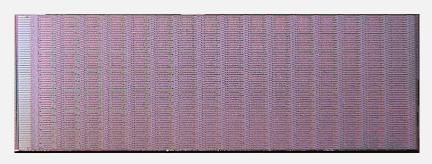
A. Caratelli, G. Bergamin, D. Ceresa, J. Kaplon, K. Kloukinas, C. Nedergaard, S. Scarfi



MPA2 ASIC

DESIGNED AND TESTED BY:

D. Ceresa, G. Bergamin, A. Caratelli, J. Kaplon, K. Kloukinas, A. Nookala, S. Scarfi (CERN EP-ESE)



Total of: ~ 185 000 chips